

Amendments to the Claims:

This listing of claims replaces all prior versions and listings of claims in the application:

Listing of Claims:

1. (Currently Amended) A process for generating ~~Process to generate~~ a structured layer (10A), comprising with the following process steps:

A) forming at least one layer (10) ~~is arranged on~~ a substrate (5),

B) generating on the at least one layer (10), a mask structure (20) with a first structure (20A) and second structure (20B) ~~is generated~~,

C) performing an isotropic process on the at least one layer (10) ~~is structured using an isotropic process, and~~

D) after performing the isotropic process, performing an anisotropic process on the at least one layer (10) ~~is then structured using an anisotropic process.~~

2. (Currently Amended) The process of claim 1, wherein the at least one layer is a first layer and the process further comprises: ~~Process as per the preceding claim to generate at least two structured layers (10A, 15A) which are arranged on top of each other on a substrate (5);~~

~~—wherein, in process-step A), forming a second layer over the first layer and (10) and over this, at least one second layer (15) are arranged,~~

~~—wherein, in process-step C), a performing the isotropic process includes structuring the second layer (15), and in process step D) the first layer (10) are structured performing the anisotropic process includes structuring the first layer.~~

3. (Currently Amended) ~~The process of claim 1, Process as per one of the preceding~~  
~~claims;~~

[[ - ]]wherein the first structure of the mask ~~structure~~ is a rough structure and the second structure of the mask ~~structure~~ is a fine structure, ~~wherein and~~ the smallest expansion of the rough structure is at least twice as large as the smallest expansion of the fine structure.

4. (Currently Amended) ~~Process as per one of the claims 2 and 3, The process of claim 2,~~

[[ - ]]wherein, ~~in process step C), performing an isotropic process includes using an~~  
~~etching agent which is selective for the second layer is utilized.~~

5. (Currently Amended) ~~Process as per one of the preceding claims~~The process of claim  
2,

[[ - ]] wherein, ~~in process step A), forming at least one of the first layer or the second~~  
~~layer includes forming a metal layer~~layers are generated as the first and / or second layers.

6. (Currently Amended) The process of claim 2,

~~Process as per the preceding claim;~~

[[ - ]]wherein, ~~in process step A), the first layer is a Pt layer is generated on the substrate~~  
~~as the first layer and the second layer is an Au layer is generated on the substrate as a second~~  
~~layer.~~

7. (Currently Amended) ~~Process as per one of the preceding claims~~ The process of claim  
1, wherein, in process step B), generating on the at least one layer a mask includes forming a  
photoresist layer is generated and structured by means of performing photolithography into a on  
the photoresist layer to form the mask structure.

8. (Currently Amended) The process of claim 2, Process as per one of the claims 2 to 7,  
[[ - ]] wherein:  
, in step C), performing the isotropic process removes the second layer below the mask structure, and is removed  
—wherein, subsequently in a process step C1), the mask structure is lowered onto the first layer in areas in which the second layer beneath the mask structure was is removed.

9. (Currently Amended) The process of claim 2Process as per one of the claims 2 to 8,  
[[ - ]] wherein,in process step C),  
performing an isotropic process includes structuring the second layer is structured by means of with wet chemical isotropic etching, and  
—wherein, in process step D), performing an anisotropic process includes structuring the first layer is structured by means of anisotropiewith a dry anisotropic etching processprocesses.

10. (Currently Amended) Process as per one of the preceding claims 2 to 9The process of claim 2, [[ - ]]wherein, in process step C), performing an isotropic process on the second layer removes the second layer entirely is removed except for one or several areas below the mask structure.

11. (Currently Amended) The process of claim 1, Process as per one of the preceding claims, [[ - ]]wherein, in a process step E) which follows D) after performing the anisotropic process, the mask structure (20) is removed.

12. (Currently Amended) The process of claim 2Process as per one of the preceding claims 2 to 11, for the production of an electrical component (1), wherein:  
—in process step A), the first layer is formed on the substrate (5) with its additional functional layers on the substrate, (36, 40, 45, 50) is provided below the first layer (10), wherein, the first and second layers (10, 15), respectively, are formed as metal layers,

~~in process step B), the first structure of the mask structure (20) with at least one is a geometrically formed area and the second structure is a linear structure (20B) that (20A) is generated as the first structure, with line formed structured (20B) originating/originates from it as the second structure the first structure,~~

~~in process step C), performing the isotropic process structures the second layer (15) is structured into an area (15A) which lies below the at least single geometrically formed area (20A) of the mask structure (20), and forms wherein a bond pad (25) is formed,~~

~~in process step D), performing the anisotropic process transfers the line formed linear structures (20B) of the mask structure (20) are transferred into the first layer (10), wherein forming contact lines (30) are formed, and~~

~~wherein the bond pad (25) possesses a form (25B) which is largely adapted to the geometric form (20A) of the geometrically formed area has approximately a shape of the mask structure and a cross section (25C) which widens towards the substrate.~~

13. (Currently Amended) The process of claim 12~~Process as per the preceding claim, [[- ]]~~wherein there are multiple linear structures and the line formed linear structures (20B) of the mask structure (20) are formed in grate arrangements.

14. (Currently Amended) An electrical ~~Electrical~~ component (1), comprising: with ~~[[ - ]]~~ a substrate (5), and  
~~wherein at least a first structure (15A) and a second (10A) structure are arranged on the substrate (5),~~

~~[[ - ]]~~wherein the first structure is structured by means of an isotropic structuring process, and the second layer structure is formed structured by means of an anisotropic structuring process and the first structure and the second structure are structured from at least one layer out of at least a single layer (10).

15. (Currently Amended) The electrical ~~Electrical~~ component as per the preceding of claim 14, [[- ]] wherein the first ~~(15A)~~structure is structured from a first layer and the second (10A) structure are is structured from differing first (10) and a second (15) layerslayer, which is different from the first layer.

16. (Currently Amended) The electrical ~~Electrical~~ component as per the preceding of claim 15,

[[ - ]] wherein the first structure has includes a bond pad (25) and the second structure has includes contact lines.

17. (Currently Amended) The electrical ~~Electrical~~ component as per the preceding of claim 16, formed as a surface wave component, wherein:

[[ - ]] ~~in which~~ the contact lines are electrically conducting microstructures, and  
[[ - ]] the substrate includes a piezoelectric crystal.

18. (Currently Amended) The electrical component of ~~Component as per claim 16,~~ [[ - ]] wherein the contact lines ~~(30)~~are formed in a grate pattern.

19. (Currently Amended) The electrical component of claim ~~Component as per one of the claims 16 to 18,~~ wherein:

[[ - ]] ~~in which~~ the contact lines (30) include a first electrically conducting material, and  
[[ - ]] the bond pad (25) includes a first electrically conducting layer and second electrically conducting layer, wherein the first layer includes a first electrically conducting material, and the second layer includes ~~the~~ a second electrically conducting material and the first layer is different from the second layer.

20. (Currently Amended) The electrical ~~Electrical~~ component as per the preceding of claim 19, ~~wherein -in which-~~ the first electrically conducting material is Pt[[.]] and the second electrically conducting material is Au.

21. (Currently Amended) The electrical component of claim ~~Component~~ as per one of the claims 14 to 20, [[- ]] wherein the substrate additionally includes active layers (36, 40, 45, 50).

22. (Currently Amended) The electrical component of claim 21, wherein the component ~~is~~ Component (1), formed as an LED as per the preceding claim, [[- ]] in which the active layers (36, 40, 45, 50) include p- and n- endowed semiconductor layers (36, 40).

23. (Currently Amended) The process of claim 1, Process as per one of the claims 1 to 13, [[- ]] ~~wherein, in process step C),~~  
performing an isotropic process transfers the first structure of the mask ~~structure into the~~  
at least one layer, and  
~~in process step D), performing an anisotropic process transfers~~ the second structure of the mask structure ~~are transferred into the at least single one layer.~~

24. (Currently Amended) The process of claim 23 Process as per the preceding claim, [[-]] ~~wherein, in process step C),~~  
performing the isotropic process only transfers the first structure into the at least one  
layer, and in process step D),  
performing the anisotropic process only transfers the second structure layer is transferred  
into the at least single one layer.

25. (Currently Amended) An electrical ~~Electrical~~ component (1), comprising:

~~—including a substrate (5) with a first structure (15A) and second structure (10A)~~  
arranged thereon,

[[ - ]] wherein the first structure (15A) possesses a cross section (15C) which widens towards the substrate (5) and a geometric form (25B) whose circumference possesses additional recessed areas (25A).

26. (Currently Amended) The electrical ~~Electrical~~ component (1) as ~~per the preceding of~~  
claim 25, [[ - ]] wherein the first structure is a rough structure and the second structure is a fine  
structure, ~~wherein~~ and the smallest extension of the rough structure is at least twice as large as  
the smallest extension of the fine structure.

27. (Currently Amended) The electrical ~~Electrical~~ component as ~~per one of the claims of~~  
claim 25, or 26, wherein the first structure ~~may, for instance, consist~~ consists of a bond pad (25),  
and the second structure of contact lines (30).